

Description

The SX3P10MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -100V$ $I_D = -3A$

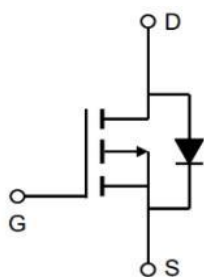
$R_{DS(ON)} < 350m\Omega$ @ $V_{GS} = -10V$

Application

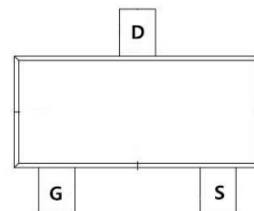
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-1.7	A
I_{DM}	Pulsed Drain Current ²	-9	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	$^\circ\text{C/W}$

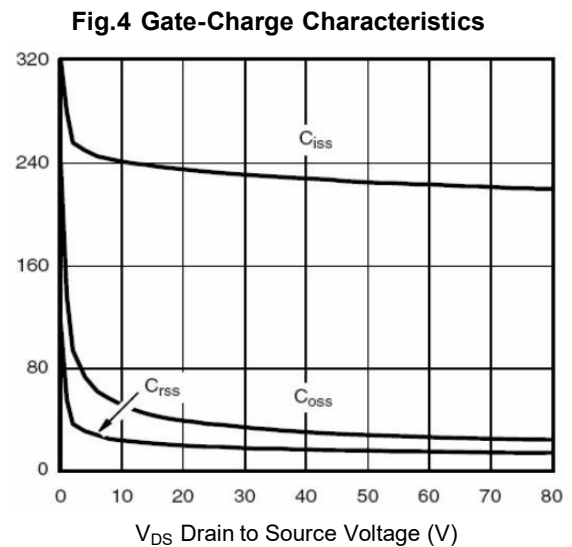
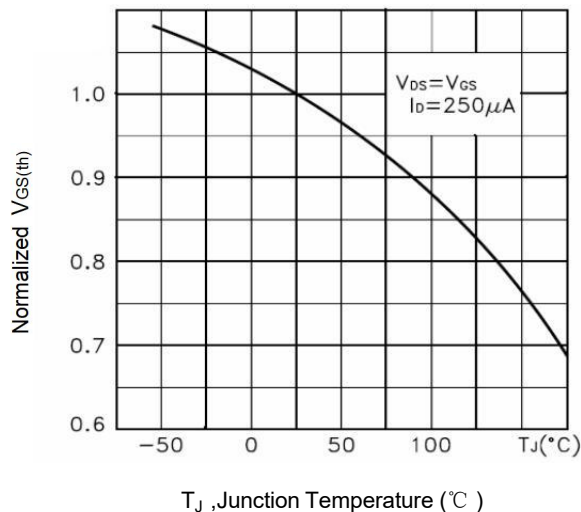
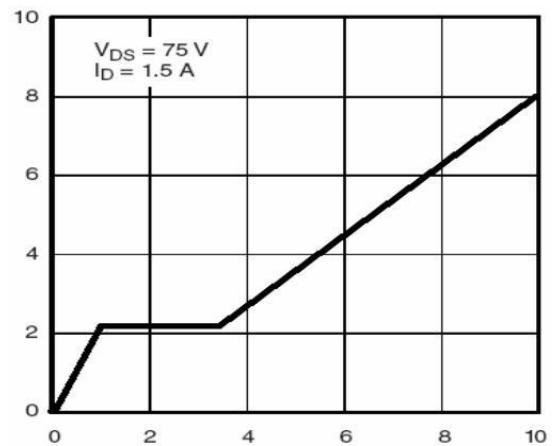
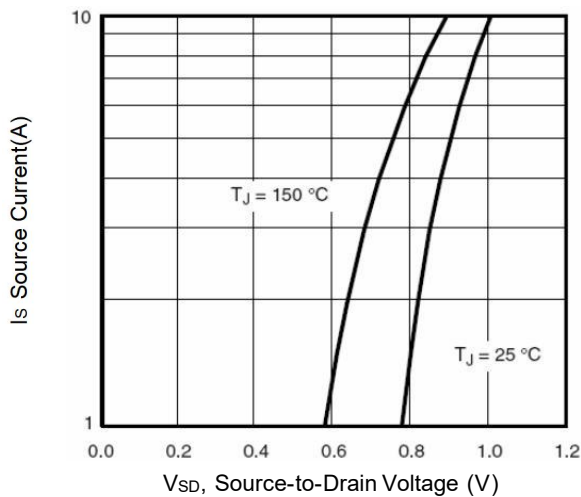
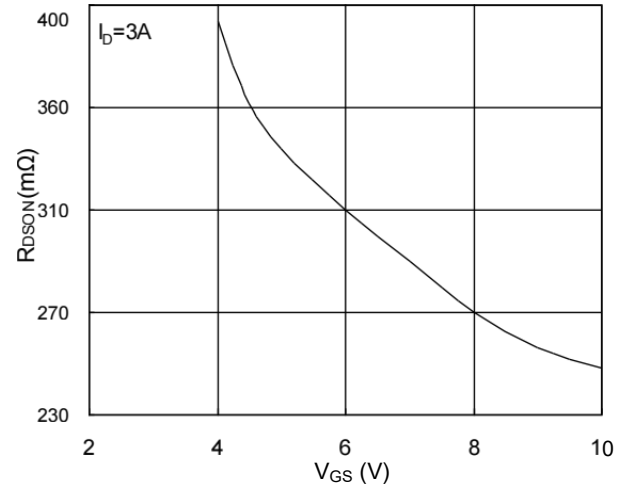
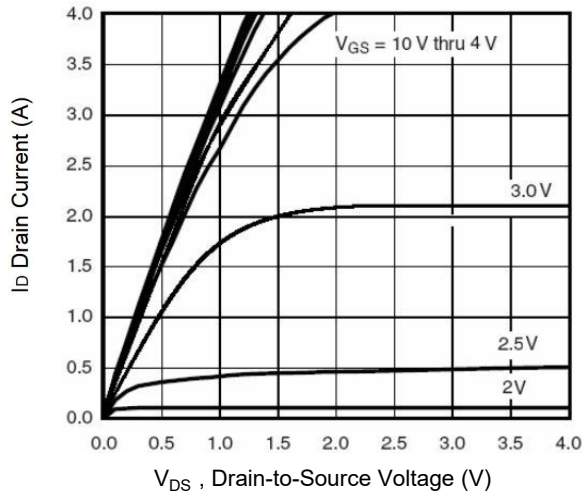
Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-100	-111	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =-1mA	---	-0.0624	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-3A	---	260	350	mΩ
		V _{GS} =-4.5V , I _D =-2A	---	320	400	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.9	-2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	4.5	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-100V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-100V , V _{GS} =0V , T _J =100°C	---	---	100	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-0.8A	---	3	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	16	32	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V , V _{GS} =-4.5V , I _D =-0.5A	---	4.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.14	---	
Q _{gd}	Gate-Drain Charge		---	1.5	---	
Td(on)	Turn-On Delay Time	V _{DD} =-50V , V _{GS} =-10V , R _G =3.3Ω I _D =-0.5A	---	17.6	---	ns
T _r	Rise Time		---	2.7	---	
Td(off)	Turn-Off Delay Time		---	4.5	---	
T _f	Fall Time		---	3	---	
Ciss	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz	---	550	---	pF
Coss	Output Capacitance		---	56	---	
Crss	Reverse Transfer Capacitance		---	35	---	
IS	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current	---	---	-3	A
ISM	Pulsed Source Current ^{2,4}		---	---	-9	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1.3	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics



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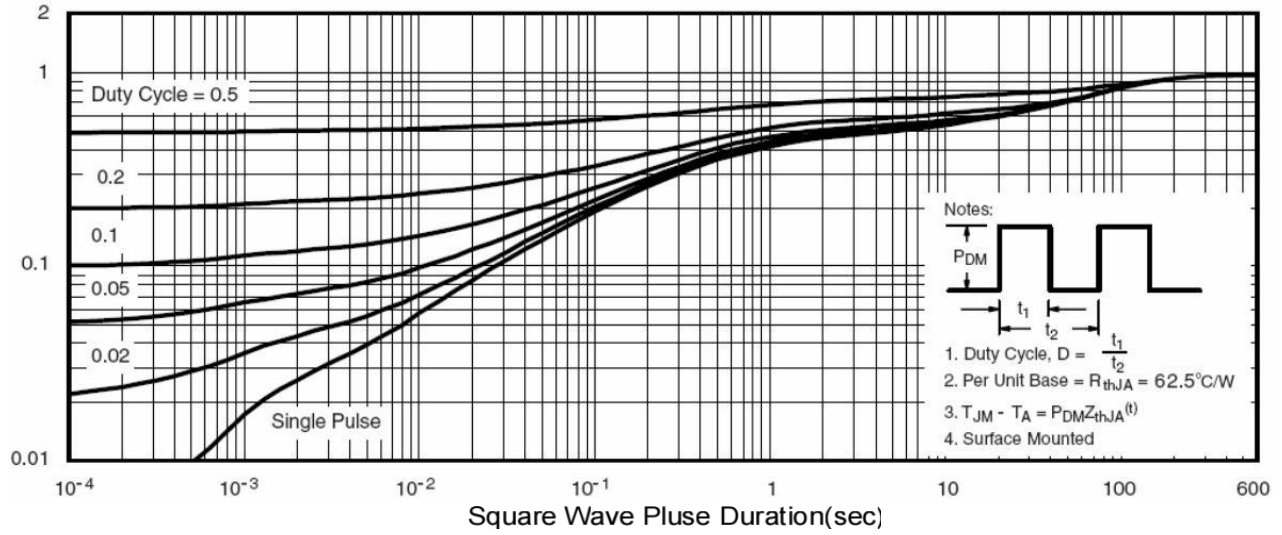


Fig.9 Normalized Maximum Transient Thermal Impedance

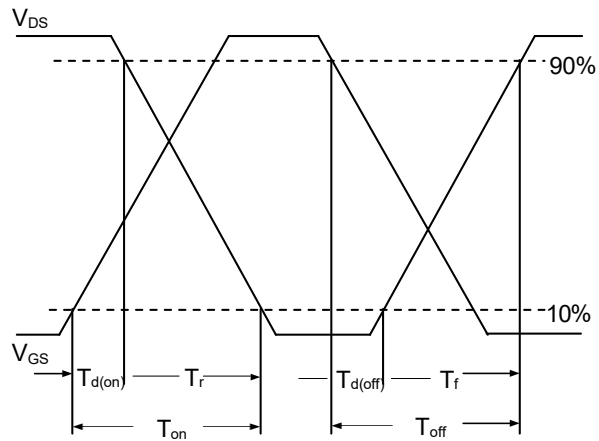


Fig.10 Switching Time Waveform

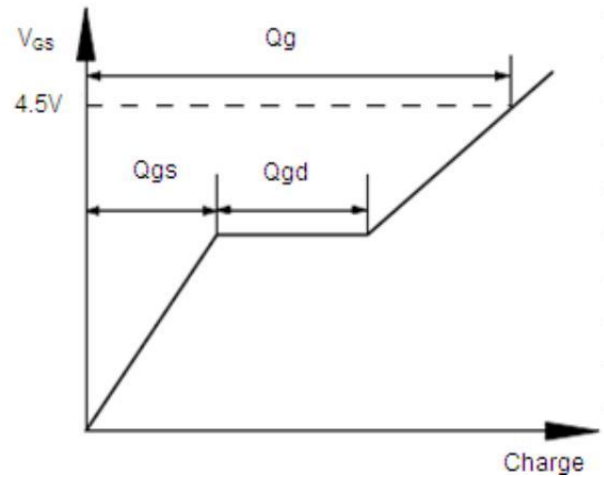
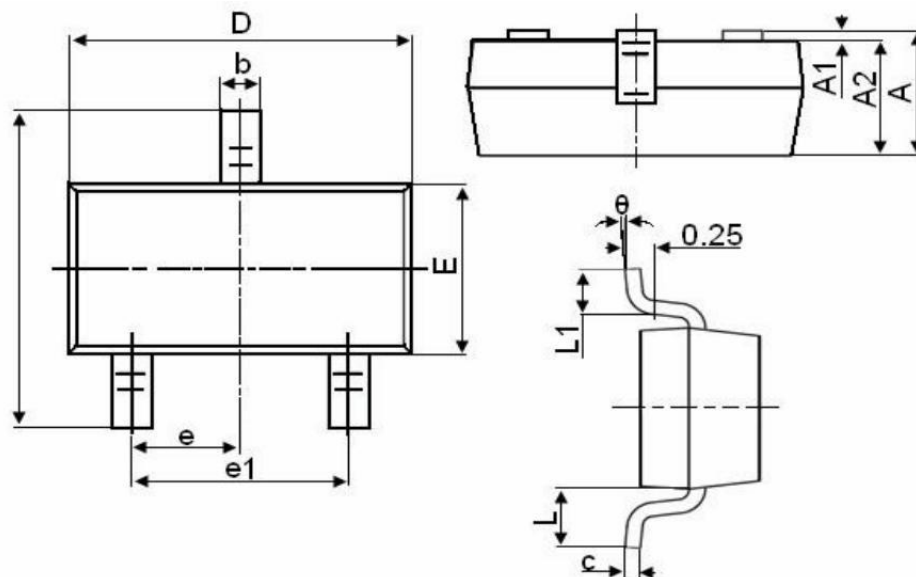


Fig.11 Gate Charge Waveform

MOSFET Package Mechanical Data: SOT23-3L



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23-3L		3000